

## Features

- Spilt Gate Trench MOSFET Technology
- Excellent Package For Heat Dissipation
- High Density Cell Design For Low  $R_{ds(on)}$
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## N-CHANNEL MOSFET

## Maximum Ratings

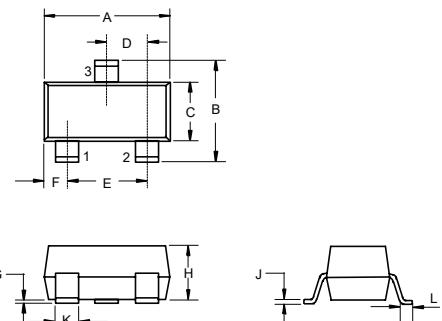
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 140°C/W Junction to Ambient<sup>(Note 2)</sup>

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $T_A=25^\circ\text{C}$	$I_D$	3	A
$T_A=70^\circ\text{C}$		2.4	
Pulsed Drain Current ( Note 3)	$I_{DM}$	12	A
Total Power Dissipation <sup>(Note 4)</sup>	$P_D$	0.9	W

### Note:

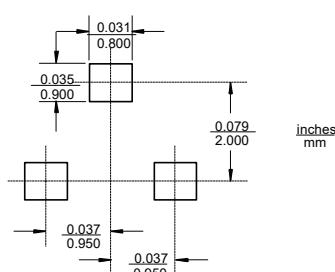
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ .
3. Repetitive rating; pulse width limited by max. junction temperature.
4. Pd is based on max. junction temperature, using junction-ambient thermal resistance.

## SOT-23

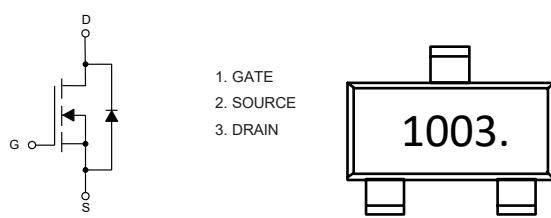


DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.110	0.120	2.80	3.04	
B	0.083	0.104	2.10	2.64	
C	0.047	0.055	1.20	1.40	
D	0.034	0.041	0.85	1.05	
E	0.067	0.083	1.70	2.10	
F	0.018	0.024	0.45	0.60	
G	0.0004	0.006	0.01	0.15	
H	0.035	0.043	0.90	1.10	
J	0.003	0.007	0.08	0.18	
K	0.012	0.020	0.30	0.51	
L	0.007	0.020	0.20	0.50	

## Suggested Solder Pad Layout



## Internal Structure and Marking Code



**Electrical Characteristics @ 25°C (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.8	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3A$		110	140	$m\Omega$
		$V_{GS}=4.5V, I_D=2A$		160	300	
Gate Resistance	$R_g$	f=1 MHz, Open drain		2.0		$\Omega$
<b>Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$				3	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=3A$		0.8	1.2	V
Reverse Recovery Time	$t_{rr}$			30		ns
Reverse Recovery Charge	$Q_{rr}$	$I_S=3A, di/dt=100A/\mu s$		25		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		135		$pF$
Output Capacitance	$C_{oss}$			28		
Reverse Transfer Capacitance	$C_{rss}$			1.2		
Total Gate Charge	$Q_g$	$V_{DS}=50V, V_{GS}=10V, I_D=3A$		3.2		$nC$
Gate-Source Charge	$Q_{gs}$			0.5		
Gate-Drain Charge	$Q_{gd}$			1.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DD}=50V, I_D=3.0A, R_G=2\Omega$		3		$ns$
Turn-On Rise Time	$t_r$			18		
Turn-Off Delay Time	$t_{d(off)}$			10		
Turn-Off Fall Time	$t_f$			18.6		

## Curve Characteristics

Fig. 1 - Typical Output Characteristics

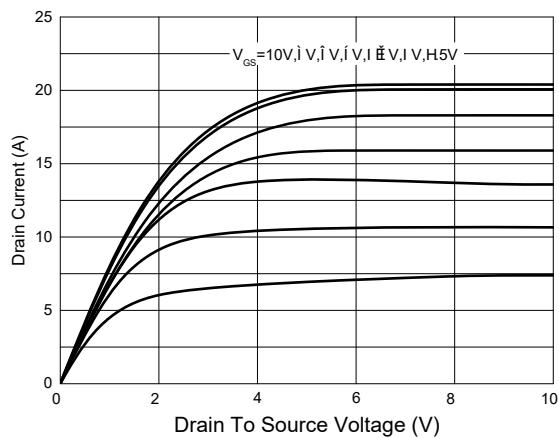


Fig.2 Transfer Characteristic

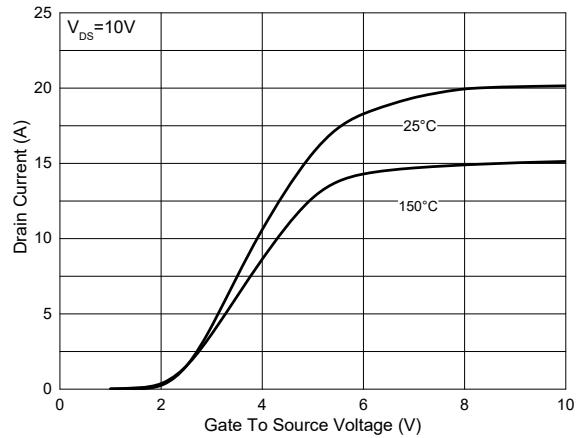


Fig.3  $R_{DSON}$ - $V_{GS}$

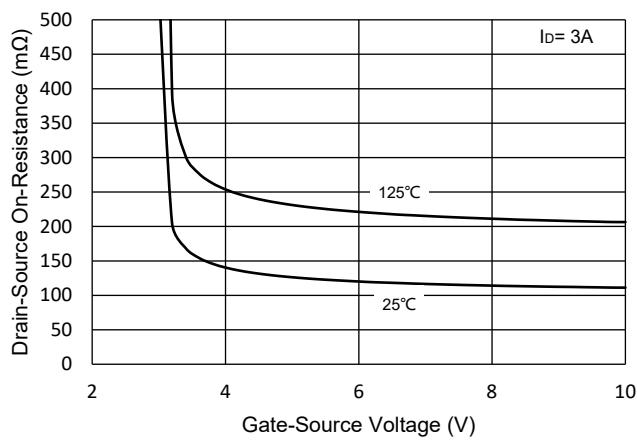


Fig.4  $R_{DS(ON)}$ - $I_D$

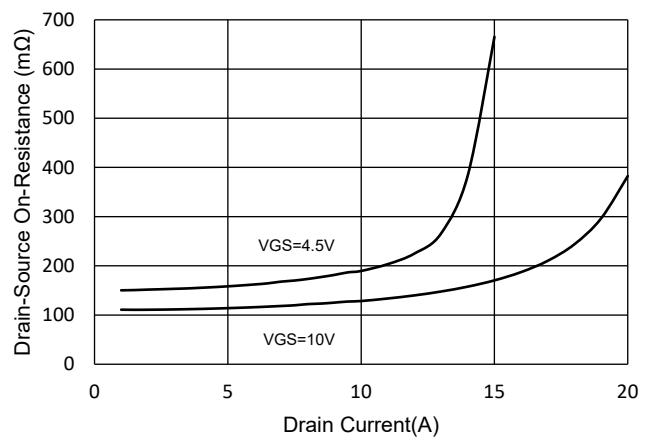


Fig.5 Capacitance Characteristics

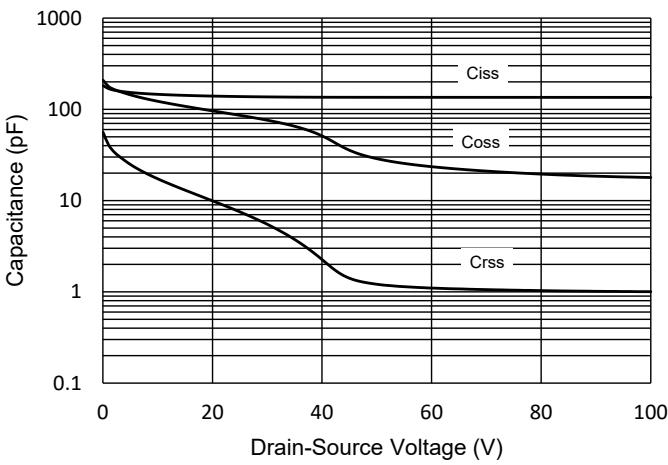
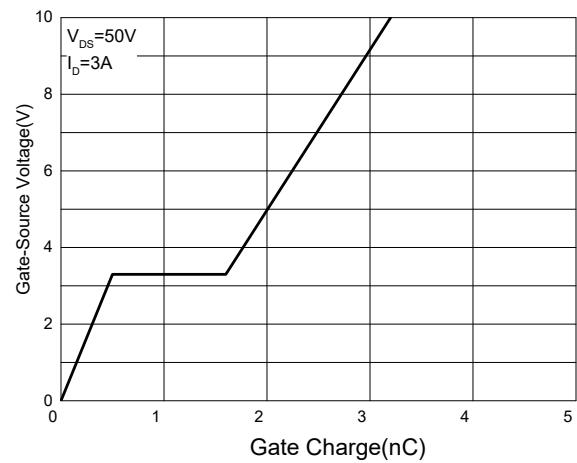


Fig. 6 - Gate Charge



## Curve Characteristics

Fig.7 Normalized Threshold Voltage

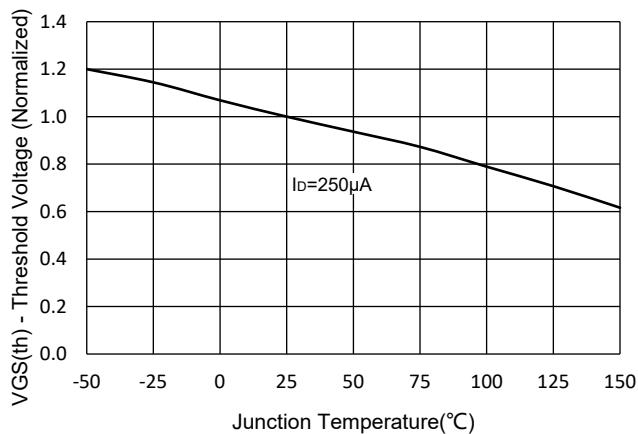


Fig.8 Normalized On Resistance Characteristics

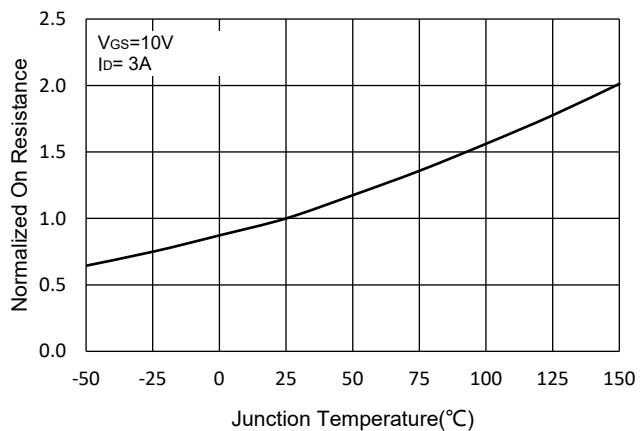


Fig.9 IS-VSD

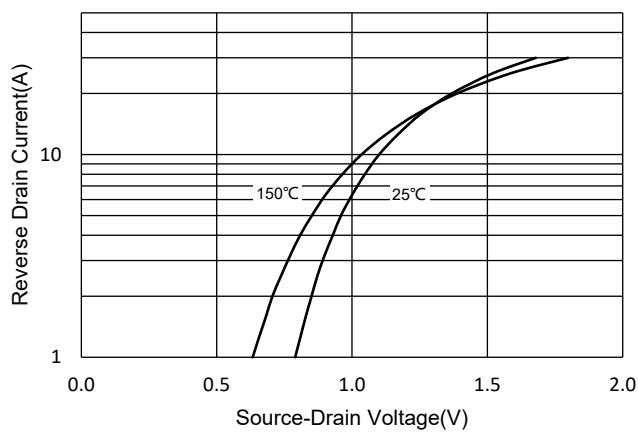


Fig.10 Drain Current

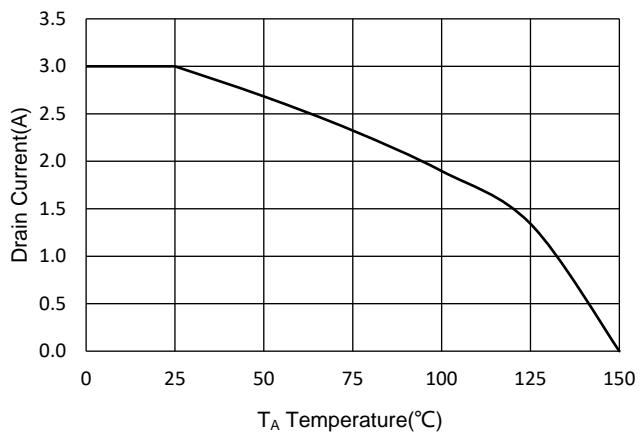
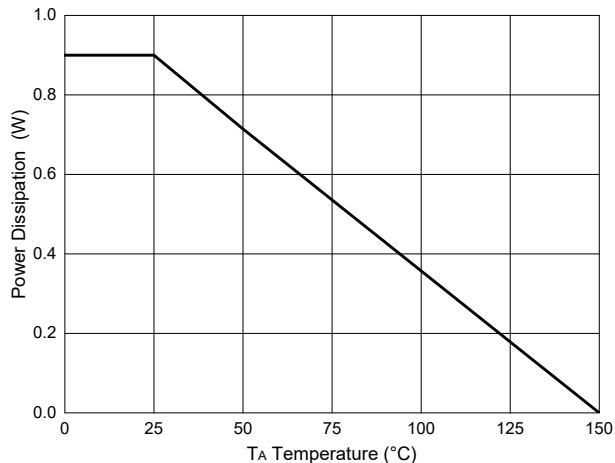


Fig.11-PD Dissipation



## Curve Characteristics

Fig. 12 - Safe Operation Area

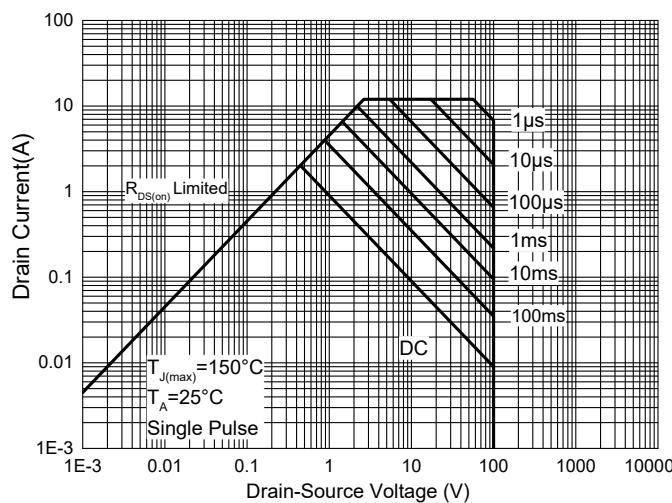
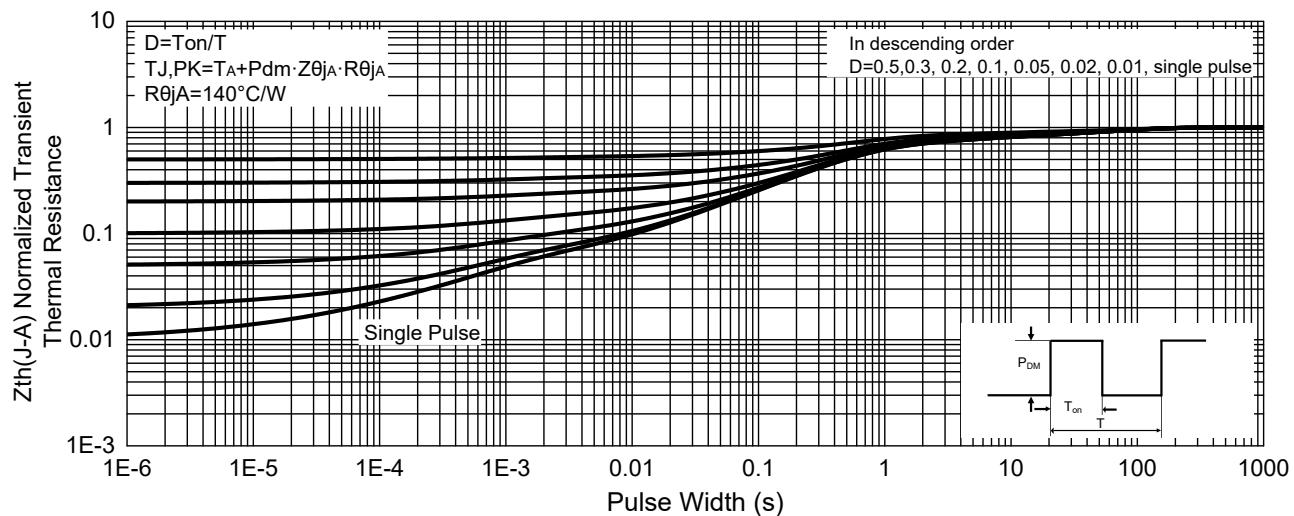


Fig. 13 -Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

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